

High Frequency High Voltage Diode

PST—2CL 500mA/12KV

Characteristics

1. High junction temperature up to 130°C
2. Low forward voltage drop, and small current leakage
3. Avalanche breakdown protection
4. Excellent properties against HV surge impact
5. Axial leading wires which are weldable
6. Epoxy package with anti-corrosion properties on surface

Application

- Rectification for microwave oven
- Industrial microwave power supplies
- HF X ray source
- Laser power supply
- Voltage multiplying circuits
- Rectification of power supplies for other electronic devices

1. Main Specification

No.	Item	Symbol	Unit	Rating	Conditions
1	Renetitive Peak Reverse	V_{RRM}	KV	12	
2	Average Forward Current	$I_{F(AV)}$	mA	500	Tamb=60 °C 50HZ Sine-half Wave Rectification Average Value
3	Forward Surge Current	I_{FSM}	A	30	Tamb=25 °C 50HZ Sine-half Wave,One Shot
4	Reverse Surge Current	I_{RSM}	μ A	0.1	Pulse width 1ms triangle wave single pulse
5	Maximum Junction Temperature	T_{jmax}	°C	130	
6	Storage Temperature	T_{stg}	°C	-40~+130	

2. Electric Specification

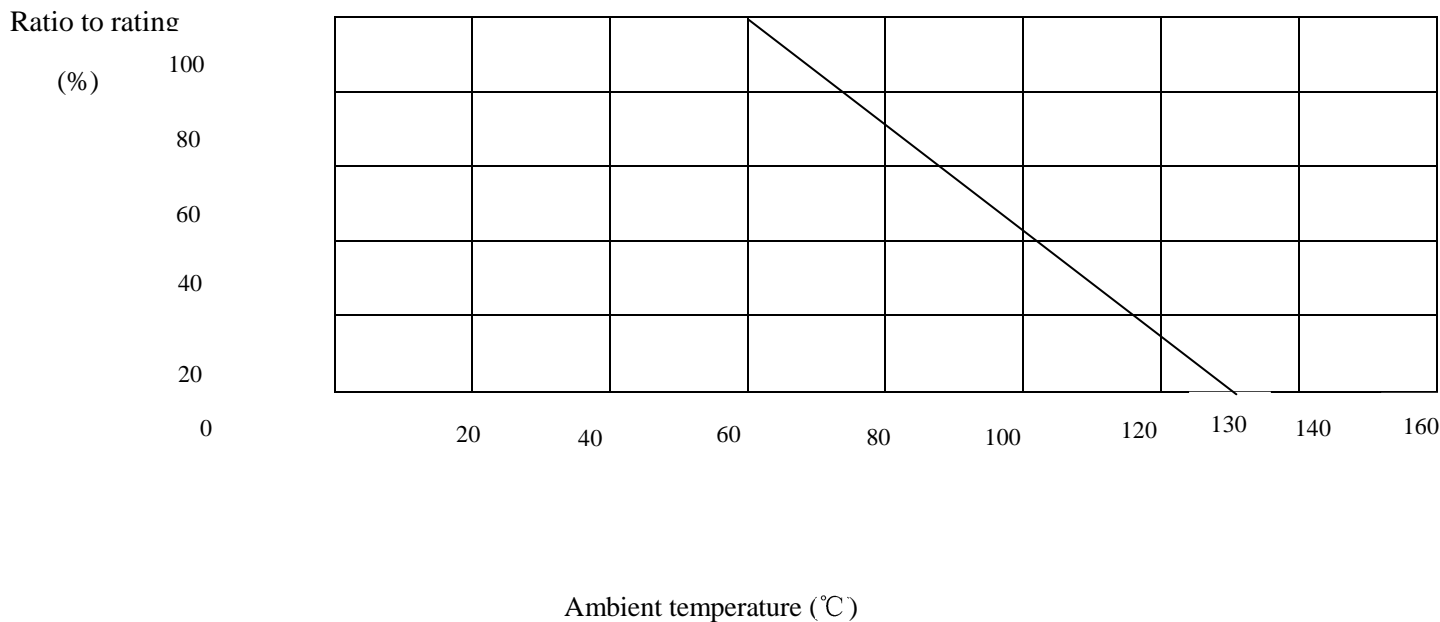
NO.	Item	Symbol	Unit		Test conditions
1	Forward Voltage Drop	V_{FM}	V	25max	$I_{FM}=500mA$
2	Normal Temperature Reverse Current	I_{RM1}	μ A	10max	$V_{RM}=12KV$
3	High Temperature Reverse Current	I_{RM2}	μ A	10max	Tamb=100°C $V_{RM}=12KV$
4	Reverse Breakdown Voltage	V_Z	KV	12	$I_R=2A$
5	Reverse Recovery Time	trr	nS	-	$I_F=2mA, I_{RM}=4mA$ 90%

(Tamb=25 °C, unless otherwise specified)

3. Application

For high voltage rectification;

4. Derating of Forward Current



On condition of provision of a fin on cathode side and air cooling)

5. Dimensions (in mm)

